

**CMSD2004S****HIGH VOLTAGE
SWITCHING DIODE****Central**TM
Semiconductor Corp.**DESCRIPTION**

The CENTRAL SEMICONDUCTOR CMSD2004S type is a silicon switching diode manufactured by the epitaxial planar process, designed for applications requiring high voltage capability.

SUPERTM
mini**SOT-323 CASE**

The following configurations are available:

CMSD2004S

DUAL, IN SERIES

MARKING CODE: B6D

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

Continuous Reverse Voltage
 Peak Repetitive Reverse Voltage
 Peak Repetitive Reverse Current
 Continuous Forward Current
 Peak Repetitive Forward Current
 Forward Surge Current, $t_p=1\ \mu\text{s}$
 Forward Surge Current, $t_p=1\ \text{s}$
 Power Dissipation
 Operating and Storage
 Junction Temperature
 Thermal Resistance

SYMBOL

V_R	240
V_{RRM}	300
I_O	200
I_F	225
I_{FRM}	625
I_{FSM}	4000
I_{FSM}	1000
P_D	250
T_J, T_{stg}	-65 to +150
Θ_{JA}	500

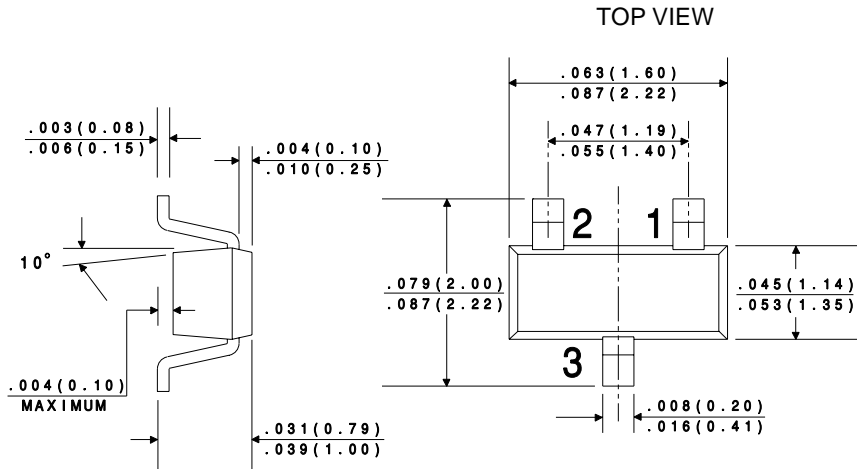
UNITS

V
 V
 mA
 mA
 mA
 mA
 mA
 mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
BV_R	$I_R=100\ \mu\text{A}$	300		V
I_R	$V_R=200\text{V}$		-	nA
I_R	$V_R=200\text{V}, T_A=150^\circ\text{C}$		-	μA
I_R	$V_R=240\text{V}$		100	nA
I_R	$V_R=240\text{V}, T_A=150^\circ\text{C}$		100	μA
V_F	$I_F=100\text{mA}$		1.0	V
C_T	$V_R=0, f=1\ \text{MHz}$		5.0	pF
t_{rr}	$I_F=I_R=30\text{mA}, \text{RECOV. TO } 3.0\text{mA}, R_L=100\ \Omega$		50	ns

All dimensions in inches (mm).



LEAD CODE

